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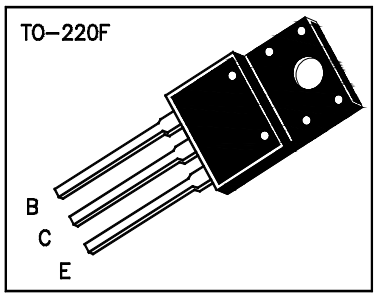
BU3150AF NPN Power Transistor



B.Base C.Collector E.Emitter

*Applications：

- ◆ Electronical Ballasts for fluorescent lighting
- ◆ Charger and Switch mode power supplies

*Features：

- ◆ High Current capacity
- ◆ High switching speed
- ◆ Wide safe operation area

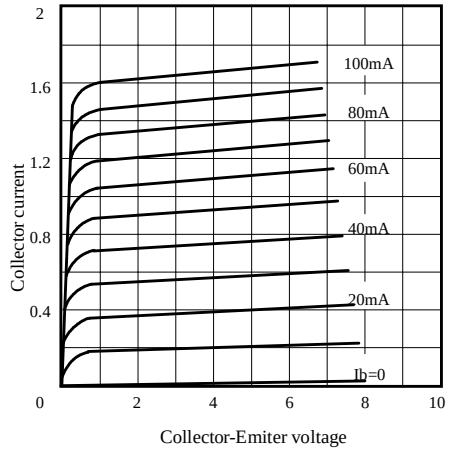
Absolute Maximum Ratings：(Tc=25℃ unless specified)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	BV_{CEO}	⩾ 800	V
Collector-Base Voltage	BV_{CBO}	⩾ 1100	V
Emitter-Base Voltage	BV_{EBO}	⩾ 9	V
Collector Current	Icm	3	A
Total Power Dissipation	Pcm	50	W
Junction Temperature	Tjm	150	℃
Storage Temperature	Tstg	－ 55 ～ 150	℃

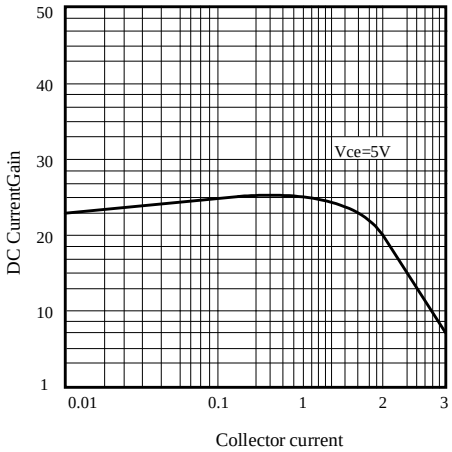
Electronical Characteristic：(Tc=25℃ unless specified)

Parameter	Symbol	Test conditions	Min.	Max.	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA； I_B=0	800		V
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=1mA； I_E=0	1100		V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=1mA； I_C=0	9		V
Collector-Emitter cut-off current	I_{CEO}	V_{CE}=750V； I_B=0		20	uA
Collector-Base cut-off current	I_{CBO}	V_{CB}=1050V ； I_E=0		10	uA
Emitter-Base cut-off current	I_{EBO}	V_{EB}=7V； I_C=0		10	uA
DC Current Gain	H_{FE}	V_{CE}=5V； I_C=0.2A	15	35	
		V_{CE}=5V； I_C=1mA	8		
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=1A； I_B=0.5A		0.6	V
Fall time	t_f	I_C=1A；I_{B1}=I_{B2}=0.2A；V_{CE}=300V		0.5	uS
Typical Frequency	f_T	V_{CE}=10V；I_C=0.1A；f =1MHz	4		MHz

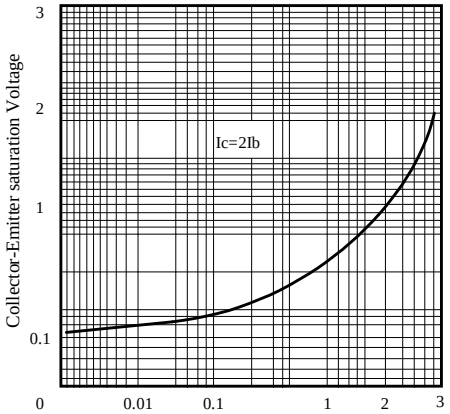
Static chatacteristic



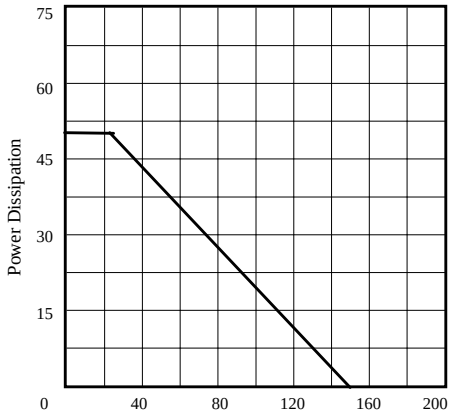
DC CurrentGain-Collector current



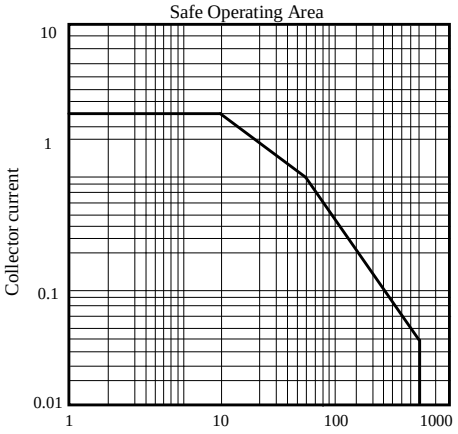
Collector-Emitter saturation -Collector current



Power Derating



Safe Operating Area



Package Dimensions

TO-220F (Unit：mm,Tolerance±0.1mm unless specified)